

## **IN THE CLAIMS:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A film deposition apparatus comprising:

a stock chamber for loading or unloading a substrate;

a transferring chamber including a first mechanism for transferring said substrate; and

a liquid phase film deposition chamber connected to said transferring chamber through a gate; and

~~an oxidization furnace connected to said liquid phase film deposition chamber through a piping,~~

wherein said ~~oxidization furnace~~ liquid phase film deposition chamber is provided with a second mechanism for oxidizing an element belonging to Group 1 or 2 of the periodic table,

~~wherein said oxidization furnace includes a third mechanism for heating said element belonging to Group 1 or 2 of the periodic table~~

wherein said second mechanism includes an oxidization cell having a lid and an oxygen gettering agent,

wherein a period of time in which said oxygen gettering agent is oxidized is adjusted by opening and closing said lid, and

wherein said oxidation cell is air-tight when said lid is closed.

2. (Original) A film deposition apparatus according to claim 1,

wherein an inside of said transferring chamber is kept under a reduced pressure and said liquid phase film deposition chamber is filled with an inert gas and is kept under atmospheric pressure or in a pressurized state.

3. (Original) A film deposition apparatus according to claim 1,  
wherein said transferring chamber is connected to a calcining chamber through a gate, and said calcining chamber is provided with a mechanism for turning said substrate upside down.

4. (Currently Amended) A film deposition apparatus comprising:  
a stock chamber for loading or unloading a substrate;  
a transferring chamber including a first mechanism for transferring the substrate; and  
a liquid phase film deposition chamber connected to said transferring chamber through a gate; ~~and~~  
~~an oxidization furnace connected to said liquid phase film deposition chamber through a~~  
~~piping,~~

wherein said ~~oxidization furnace~~ liquid phase film deposition chamber is provided with , via  
a piping, a second mechanism for oxidizing an element belonging to Group 1 or 2 of the periodic table ~~and a shutter for shutting off oxygen to said second mechanism,~~

~~wherein said oxidization furnace includes a third mechanism for heating said element~~  
~~belonging to Group 1 or 2 of the periodic table~~

wherein said second mechanism includes an oxidization cell having a lid and an oxygen  
gettering agent,

wherein a period of time in which said oxygen gettering agent is oxidized is adjusted by opening and closing said lid, and

wherein said oxidation cell is air-tight when said lid is closed.

5. (Original) A film deposition apparatus according to claim 4,

wherein an inside of said transferring chamber is kept under a reduced pressure and said liquid phase film deposition chamber is filled with an inert gas and is kept under atmospheric pressure or in a pressurized state.

6. (Original) A film deposition apparatus according to claim 4,

wherein said transferring chamber is connected to a calcining chamber through a gate, and said calcining chamber is provided with a mechanism for turning said substrate upside down.

7. (Currently Amended) A film deposition apparatus comprising:

a stock chamber for loading or unloading a substrate;

two transferring chambers each connected to said stock chamber through a gate;

a vapor phase film deposition chamber connected to one of said two transferring chambers through a gate; and

a liquid phase film deposition chamber connected to another said transferring chamber through a gate; and

~~an oxidization furnace connected to said liquid phase film deposition chamber through a~~  
~~piping,~~

wherein said ~~oxidization furnace~~ liquid phase film deposition chamber is provided with a ~~first~~ mechanism for oxidizing an element belonging to Group 1 or 2 of the periodic table,

~~wherein said oxidization furnace includes a second mechanism for heating said element~~  
~~belonging to Group 1 or 2 of the periodic table~~

wherein said second mechanism includes an oxidization cell having a lid and an oxygen  
gettering agent.

wherein a period of time in which said oxygen gettering agent is oxidized is adjusted by  
opening and closing said lid, and

wherein said oxidation cell is air-tight when said lid is closed.

8. (Previously presented) A film deposition apparatus according to claim 7,

wherein an inside of one of said transferring chambers is kept under a reduced pressure and said liquid phase film deposition chamber is filled with an inert gas and is kept under atmospheric pressure or in a pressurized state.

9. (Previously presented) A film deposition apparatus according to claim 7,

wherein one of said transferring chambers is connected to a calcining chamber through a gate, and said calcining chamber is provided with a mechanism for turning said substrate upside down.

10. (Currently Amended) A film deposition apparatus comprising:

a stock chamber for loading or unloading a substrate;

two transferring chambers each connected to said stock chamber through a gate;

a vapor phase film deposition chamber connected to one of said two transferring chambers through a gate; and

a liquid phase film deposition chamber connected to another said transferring chamber through a gate; and

~~an oxidization furnace connected to said liquid phase film deposition chamber through a piping,~~

wherein said ~~oxidization furnace~~ liquid phase film deposition chamber is provided with , via a piping, a first mechanism for oxidizing an element belonging to Group 1 or 2 of the periodic table and a shutter for shutting off oxygen to said first mechanism,

~~wherein said oxidization furnace includes a second mechanism for heating said element belonging to Group 1 or 2 of the periodic table~~

wherein said second mechanism includes an oxidization cell having a lid and an oxygen gettering agent,

wherein a period of time in which said oxygen gettering agent is oxidized is adjusted by opening and closing said lid, and

wherein said oxidation cell is air-tight when said lid is closed.

11. (Previously presented) A film deposition apparatus according to claim 10,

wherein an inside of one of said transferring chambers is kept under a reduced pressure and said liquid phase film deposition chamber is filled with an inert gas and is kept under atmospheric pressure or in a pressurized state.

12. (Previously presented) A film deposition apparatus according to claim 10,

wherein one of said transferring chambers is connected to a calcining chamber through a gate, and said calcining chamber is provided with a mechanism for turning said substrate upside down.

13. (Currently Amended) A film deposition apparatus comprising:

- a stock chamber for loading or unloading a substrata;
- a transferring chamber for transferring said substrate; and
- an EL material deposition chamber connected to said transferring chamber through a gate;

and

- ~~an oxidization furnace connected to said EL material deposition chamber through a piping,~~
- wherein said EL material deposition chamber is provided with a cell which contains an element belonging to Group 1 or 2 of the periodic table,
- ~~wherein said oxidization furnace includes a mechanism for heating said element belonging to Group 1 or 2 of the periodic table~~
- wherein said second mechanism includes an oxidization cell having a lid and an oxygen gettering agent,
- wherein a period of time in which said oxygen gettering agent is oxidized is adjusted by opening and closing said lid, and
- wherein said oxidation cell is air-tight when said lid is closed.

14. (Original) A film deposition apparatus according to claim 13,

wherein an inside of said transferring chamber is kept under a reduced pressure and said EL material deposition chamber is filled with an inert gas and is kept under atmospheric pressure or in a pressurized state.

15. (Original) A film deposition apparatus according to claim 13,  
wherein said transferring chamber is connected to a calcining chamber through a gate, and said calcining chamber is provided with a mechanism for turning said substrate upside down.

16. (Currently Amended) A film deposition apparatus comprising:  
a stock chamber for loading or unloading a substrate;  
two transferring chambers each connected to said stock chamber through a gate;  
a vapor phase film deposition chamber connected to one of said two transferring chambers through a gate; and  
an EL material deposition chamber connected to another said transferring chamber through a gate; and  
~~an oxidization furnace connected to said EL material deposition chamber through a piping,~~  
wherein said EL material deposition chamber is provided with a cell which contains an element belonging to Group 1 or 2 of the periodic table,  
~~wherein said oxidization furnace includes a mechanism for heating said element belonging to Group 1 or 2 of the periodic table~~  
wherein said second mechanism includes an oxidization cell having a lid and an oxygen gettering agent.

wherein a period of time in which said oxygen gettering agent is oxidized is adjusted by opening and closing said lid, and

wherein said oxidation cell is air-tight when said lid is closed.

17. (Previously presented) A film deposition apparatus according to claim 16,

wherein an inside of one of said transferring chambers is kept under a reduced pressure and said EL material deposition chamber is filled with an inert gas and is kept under atmospheric pressure or in a pressurized state.

18. (Previously presented) A film deposition apparatus according to claim 16,

wherein one of said transferring chambers is connected to a calcining chamber through a gate, and said calcining chamber is provided with a mechanism for turning said substrate upside down.

19-30. (Canceled)

31. (Previously presented) A film deposition apparatus according to claim 1,

wherein said liquid phase film deposition chamber is a chamber for depositing an EL material.

32. (Previously presented) A film deposition apparatus according to claim 1,

wherein said liquid phase film deposition chamber is provided with a spin coater for forming an EL layer.



33. (Previously presented) A film deposition apparatus according to claim 1, wherein said liquid phase film deposition chamber is provided with a nozzle for forming an EL layer.

34. (Previously presented) A film deposition apparatus according to claim 4, wherein said liquid phase film deposition chamber is a chamber for depositing an EL material.

35. (Previously presented) A film deposition apparatus according to claim 4, wherein said liquid phase film deposition chamber is provided with a spin coater for forming an EL layer.

36. (Previously presented) A film deposition apparatus according to claim 4, wherein said liquid phase film deposition chamber is provided with a nozzle for forming an EL layer.

37. (Previously presented) A film deposition apparatus according to claim 7, wherein said liquid phase film deposition chamber is a chamber for depositing an EL material.

38. (Previously presented) A film deposition apparatus according to claim 7, wherein said liquid phase film deposition chamber is provided with a spin coater for forming an EL layer.

39. (Previously presented) A film deposition apparatus according to claim 7,

wherein said liquid phase film deposition chamber is provided with a nozzle for forming an EL layer.

40. (Previously presented) A film deposition apparatus according to claim 10,  
wherein said liquid phase film deposition chamber is a chamber for depositing an EL material.

41. (Previously presented) A film deposition apparatus according to claim 10,  
wherein said liquid phase film deposition chamber is provided with a spin coater for forming an EL layer.

42. (Previously presented) A film deposition apparatus according to claim 10,  
wherein said liquid phase film deposition chamber is provided with a nozzle for forming an EL layer.

43. (Previously presented) A film deposition apparatus according to claim 13,  
wherein said EL material deposition chamber is provided with a spin coater for forming an EL layer.

44. (Previously presented) A film deposition apparatus according to claim 13,  
wherein said EL material deposition chamber is provided with a nozzle for forming an EL layer.

45. (Previously presented) A film deposition apparatus according to claim 16,

wherein said EL material deposition chamber is provided with a spin coater for forming an EL layer.

46. (Previously presented) A film deposition apparatus according to claim 16, wherein said EL material deposition chamber is provided with a nozzle for forming an EL layer.

47 – 52. (Canceled)

53. (Currently Amended) A film deposition apparatus according to claim 1, wherein said ~~third~~ second mechanism includes a heater.

54. (Currently Amended) A film deposition apparatus according to claim 4, wherein said ~~third~~ second mechanism includes a heater.

55. (Previously Presented) A film deposition apparatus according to claim 7, wherein said second mechanism includes a heater.

56. (Previously Presented) A film deposition apparatus according to claim 10, wherein said second mechanism includes a heater.

57. (Currently Amended) A film deposition apparatus according to claim 13, wherein said second mechanism includes a heater.

58. (Currently Amended) A film deposition apparatus according to claim 16, wherein said second mechanism includes a heater.

59. (Currently Amended) A film deposition apparatus comprising:  
a liquid phase film deposition chamber;  
~~an oxidization furnace connected to said liquid phase film deposition chamber through a~~  
~~pipng,~~  
wherein said ~~oxidization furnace~~ liquid phase film deposition chamber is provided with a  
~~cell which contains an element belonging to Group 1 or 2 of the periodic table~~ a mechanism for  
oxidizing an element belonging to Group 1 or 2 of the periodic table,  
~~wherein said oxidization furnace includes a mechanism for heating said element belonging~~  
~~to Group 1 or 2 of the periodic table~~  
wherein said mechanism includes an oxidization cell having a lid and an oxygen gettering  
agent,  
wherein a period of time in which said oxygen gettering agent is oxidized is adjusted by  
opening and closing said lid, and  
wherein said oxidation cell is air-tight when said lid is closed.

60. (Previously Presented) A film deposition apparatus according to claim 59, wherein said liquid phase film deposition chamber is a chamber for depositing an EL material.

61. (Previously Presented) A film deposition apparatus according to claim 59, wherein said liquid phase film deposition chamber is provided with a spin coater for forming an EL layer.

62. (Previously Presented) A film deposition apparatus according to claim 59, wherein said liquid phase film deposition chamber is provided with a nozzle for forming an EL layer.